HFZT

2N5400

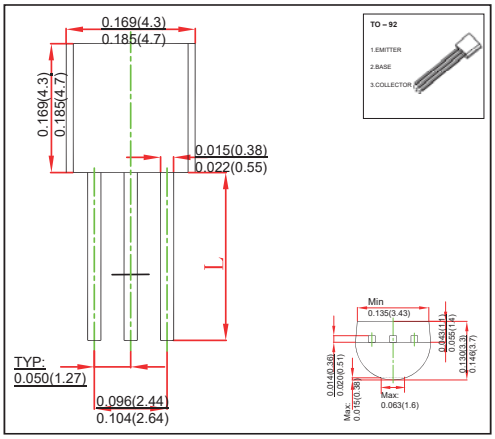
TO-92 Plastic-Encapsulate Transistors

FEATURE

- Switching and Amplification in High Voltage Applications such as elephony
- Low Current(max. 600mA)
- High Voltage(max.130v)
- TRANSISTOR (PNP)

MECHANICAL DATA

- Case style:TO-92 molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-130	V
Collector-Emitter Voltage	V_{CEO}	-120	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current -Continuous	I_C	-0.6	A
Collector Power Dissipation	P_D	625	mW
Thermal Resistance, junction to Ambient	$R_{K\ JA}$	200	℃ /W
Junction Temperature	T_j	150	℃
Storage Temperature	T_{stg}	-55 ~ +150	℃

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-100μA, I_E=0	-130			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-1mA, I_B=0	-120			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E= -10μA, I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}= -100 V, I_E=0			-0.1	uA
Emitter cut-off current	I_{EBO}	V_{EB}= -3 V, I_C=0			-0.1	uA
DC current gain	h_{FE1}	V_{CE}= -5 V, I_C=-1mA	30			
	h_{FE2}	V_{CE}= -5 V, I_C= -10mA	40		180	
	h_{FE3}	V_{CE}= -5 V, I_C=-50mA	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C= -10mA, I_B= -1mA			-0.2	V
	$V_{CE(sat)}$	I_C= -50mA, I_B= -5mA			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C= -10mA, I_B= -1mA			-1	V
	$V_{BE(sat)}$	I_C= -50mA, I_B= -5mA			-1	V
Transition frequency	f_T	V_{CE}=-10V, I_C=-10mA f =30MHz	100			MHz
Collector output capacitance	C_{ob}	V_{CB}=-10V,I_E=0,f=1MHz			6	pF